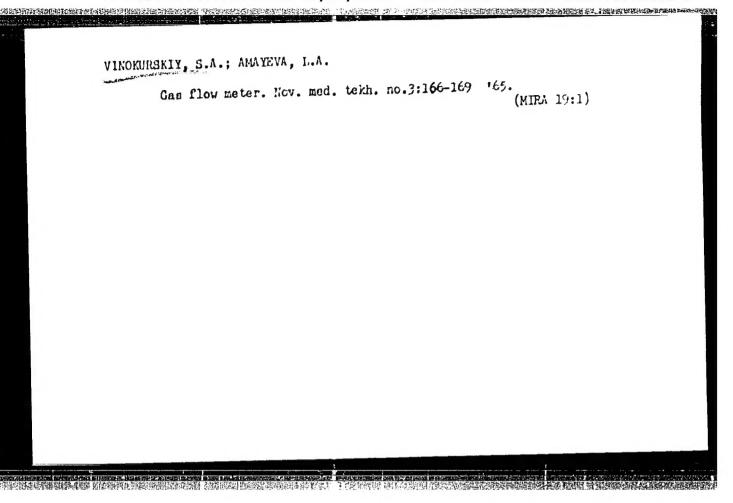
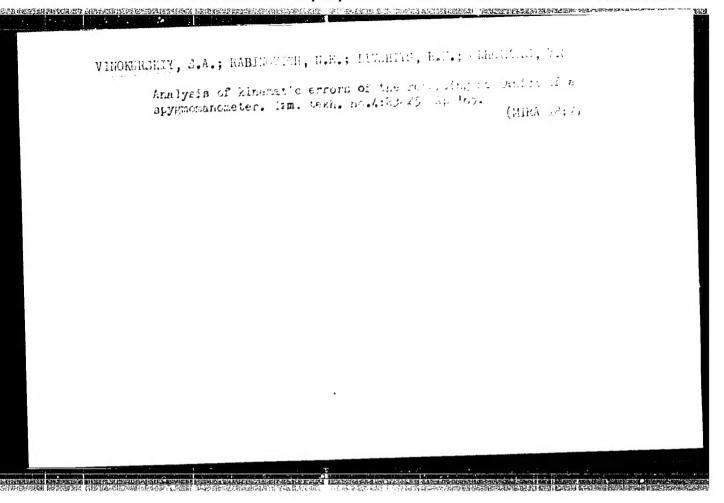
VIII	OKURSKIY, S.A.; RABINOVICH,  IDA-1 apparatus for au	tomatic measurement	of the arterial
	pressure. Nov. med. te	ekh. no.2:31-40 64.	(MIRA 18:11)

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	VINOKURSKIY, S.A.; GINZBURG, Kh.B.
	Manual flat apping dynamometer DRP-1. Nov. med. tekh.
	no.2:66-68 164. (MIRA 18:11)
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VINOKURSKIY, S.A.; GONCHARSKIY, L.A.; RABINOVICH, N.E.

Mechanotron with increased sensitivity to current changes. Trudy
VNIIMIO no.3:179-181 '63 (MIRA 18:2)

Security Same by Same

BUNIN, A.Ya.; KOZLOVA, L.P.; VINOKUKSKIY, S.A.; STETSIN, A.A.

New indicator of intraocular pressure and the results of its use. Uch.zap. GNII glaz.bol. no.8:189-193'63. (MIRA 16:9)

1. Gosudarstvennyy nauchno-issledovatel'skiy institut glaznykh bolezney imeni Gel'mgol'tsa (for Bunin, Kozlova). 2. Vsesoyuznyy nauchno-issledovatel'skiy institut meditsinskogo instrumentariya i oborudovaniya. (for Vinokurskiy, Stetsin).

(EYE, INSTRUMENTS AND APPARATUS FOR)

(INTRACCULAR PRESSURE)

BUNIN, A.Ya. kand.med.nauk; KOZLOVA, L.P.; VINOKURSKIY, S.A., kand. technicheskikh nauk; STEISIN, A.A.

New indicator of intraocular pressure and the results of its use in preventive examinations. Vest. oft. 76 no.1:75-76 (MIRA 16:6) Ja-F:63.

1. Gosudarstvennyy nauchno-issledovatel'skiy institut glaznykh bolezney imeni Gel'mgol'tsa i Vsesoyuznyy nauchno-issledovatel'skiy institut meditsinskogo instrumentariya i oborudovaniya.

(EYE, INSTRUMENTS AND APPARATUS FOR)
(INTRAOCULAR PRESSURE)

VINOKURSKIY, S.A.; GINZBURG, Kh.B.; KORYAKIN, M.F.

Reverse dynamometer for determining the force of weakened muscles. Med. prom. 15 no.6:57-59 Je '61. (MIRA 15:3)

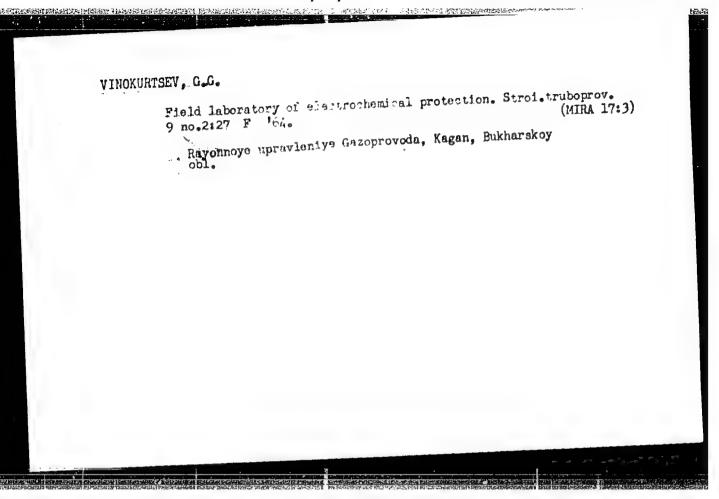
VINOKURSKIY, S.A.; VOTCHAL, B.Yo.; AMAYEVA, L.A.

Arterial oscillometer. Med.prom. 15 no.9:48-50 S '61. (MIRA 14:9)

1. Vsesoyuznyy nauchno-issledovatel'skiy institut meditsinskikh instrumentov i oborudovaniya i TSentral'nyy institut usovershenstvo-vaniya vrachey.

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	AUTHOR: Vinokurtaev, G. G. ORG: Gas Pipeline Administration, Tashkent (Upravleniye magistral nykh gazoprovodov) TITLE: Planning means for electrochemical protection with comprehensive consideration
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	TOPIC TAGS: pipeline, electrochemistry  Approach: One reason for the inadequate protection from soil corrosion of the
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	100 ohm/m. Where they will measurement and planning
	be drawn up, with more attention paid to dareful added to take a lateral added and consideration of local conditions. Orig. art. has: 1 table. [JPRS]
	SUB CODE: 13, 07 / SUEM DATE: none
	UDC: 621.643.001.12
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VINOXURTSEV, G.G.

Electrochemical protection of gas pipelines in Central Asia. Gaz.

(MIRA 18:1)

delc no.20:24-27 \*[64.

1. Tashkentskoye upravlenive magistral nykh gazoprovodov.

When automats were established. Obshchestv. pit. no.7:61-62 (MIRA 12:12)
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1.Direktor tresta restoranov i kafe, Leningrad. (LeningradRestaurants, lunchrooms, etc.)

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VINOPAL

CZECHOSLCVAKIA/Electronics - Electrocells and Semiconductors

Device

: Ref Zhur Fizika, No 9, 1959, 20783 Abs Jour

: Frank, Helmar; Vinopal, Jarcmir A thor

Inst

: Silicon Junction Rectifiers Title

Slabopro dy obzor, 1958, 19, No 10, 639-643 Orig Pub

: After a examination of various types of rectifiers, Abstract

the a thors describe the properties of silicon junction diodes. Comparison of the properties of silicon and germanium diodes is accompanied by a brief explanation on the basis of the band theory. Pata are given (including curves for the equations and tables for the parameters), which characterize the properties of silicon junction diodes (types 111 - 124 NP70), designed for voltages up to 300 and currents up to 1 amp, partic larly their behavior at higher temperat res. Bibliography, 13 titles.

Card 1/1

VINOPAL, Jaromir, inz., dr.; PISA, Gustav, inz.

Metallurgy of semiconductor pn junctions. Hut listy 17 no.10:712-720 0 162.

1. Ceskomoravska-Kolben-Danek Praha.

VINOPAL, J., inz., dr.; PISA, G., inz.

Silicon electric power rectifiers. Energetika Cz ll
no.3:1/43-144 Mr '61.

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9.4300 (1035, 1138, 1143)

Z/017/60/C49/011/008/013 E073/E535

AUTHORS:

Pisa, Gustav, Engineer, Spiess, Petr, Engineer, Sebek, Švatopluk, Engineer, Vendlerova, Vera, Engineer

and Vinopal, Jaromir, Engineer Doctor

TITLE:

New Knowledge Gained in the Development of the Technology of Germanium and Silicon Rectifier Elements

PERIODICAL: Elektrotechnický obzor, 1960, Vol.49, No.11, pp.579~583

In addition to reviewing world trends in semiconductor development, the authors deal briefly with results of development work in the Semiconductor Laboratories of CKD. Prague. The problem of dislocations in germanium has been dealt with extensively in Czech as well as in foreign literature (Refs. 3,4,5). Therefore, the authors deal only briefly with the results of extensive experiments, the aim of which was to determine the influence of the absolute number of dislocations on the quality of the P-N junctions and the influence of accumulation of dislocations and of microscopically visible disturbances caused by accumulation of dislocations within a small volume. A more detailed treatment of these is given in a paper by Burger and

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New Knowledge Gained in the Development of the Technology of Germanium and Silicon Rectifier Elements

Sebek which is in the process of publication. In the experiments three germanium single crystals have been used which have a satisfactory specific resistance and a lifetime of the minority carriers. All these three crystals contained in some spots very pronounced grouping of dislocations in the form of lines and stripes. All the cut plates were etched in order to make the dislocations visible. The locations of the disturbances were marked in detail. In order to be able to make a good comparison test discs of 12 mm diameter were cut from these specimens. These could be sub-divided into three groups:

- a) Plates from locations which did not contain accumulations of dislocations but only uniformly distributed dislocations:
- b) Plates from locations that contained slight accumulations of dislocations in the nature of stripes,
- c) Plates from locations that contained considerable line dislocations formed by a large quantity of dislocations. A total of about 150 such plates were investigated which originated

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New Knowledge Gained in the Development of the Technology of Germanium and Silicon Rectifier Elements

from three germanium crystals. The characteristics of the three types of discs are reproduced in Fig.l and it can be seen that the diode of the group (c) reaches only about 40% of the voltage of the diodes of group (a). All the results obtained for the three groups of diodes were used for plotting average value These are similar to the curves in Fig. 2. characteristics of diodes from group (b) were below those of group (a) and on the average were nearer to those of group (c). The experiments have shown the quality of the P-N transitions is decisively influenced by the poorest transition spot, i.e. by the spot that contains a high accumulation of dislocations and it is this spot which determines the properties of the P-N junction. In studying the inverse voltages of diodes, investigations were made on materials with various average numbers of dislocations between zero and several tens of thousands per cm2. As a result, the dependence was determined of the inverse voltage of junction rectifiers on the number of Card 3/6

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dislocations, provided that the dislocations are uniformly distributed, without considerable accumulations of stripes or lines. It was found that within wide limits this dependence is not greatly affected by the absolute number of dislocations. provided that these are uniformly distributed. Only in the case of high densities, i.e. above 2 x 10 /cm2, will there be a considerable drop of the average voltage of the diodes. The P-N transitions of germanium were first etched electrolytically by means of a hydrofluoric acid and then were etched again with a mixture, the main component of which was hydrogen peroxide with additions of nitric, acetic and hydrofluoric acid. The effect of this new etching mixture was tested on a large number of diodes. The inverse voltage improved considerably, on the average by 100 V, as also did the inverse current (Table 1 and Fig. 2). However, the surface of the diode is much more sensitive to the atmosphere and it was necessary to develop a new method of protecting the junctions. For this purpose silicon Card 4/6

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varnishes and silicon vaseline were used but these did not prove satisfactory. Subsequently, polymer type synthetic materials were used for this purpose and the characteristics of a diode after etching with hydrofluoric acid, the above mentioned etching mixture and protection by embedding in a synthetic material, are plotted in Fig. 3. For the manufacture of silicon P-N junctions with inverse voltages exceeding 1000 V it is advisable to use silicon with a specific resistance of 100 to 300 0hm cm and a minimum lifetime of the minority carriers of 200 to 300 usec with a homogeneous crystal lattice and without internal stresses and undesirable disturbances. Several methods of etching of silicon plates in etching agents of various compositions were tested. The speed and the depth of etching increases with the concentration of the etching agent and with temperature. The decrease in the thickness as a function of the etching time in various etching agents is plotted in Fig. 4. For 150 A rectifiers, a junction area of 200 mm<sup>2</sup> was chosen in order to obtain longer service life, better heat removal and to avoid excessive over-loading when the Card 5/6

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junctions are fully loaded. ČKD manufactures rectifier systems with N-type silicon with junctions produced by the fusion method in vacuum. Type N silicon is the most easily available in Czecho. slovakia and so far has proved satisfactory. Manufacture of P-N junctions by the diffusion method is also being studied, since it is considered to be more suitable for P-N-P-N junctions. The best method of protecting P-N silicon junctions from the effects of the atmosphere is to encapsule them in vacuum-tight containers. In tests so far good results have been obtained by protecting the junctions with a silicon vaseline prepared in the Research Institute for Organic Synthesis without any addition the vaseline must be absolutely pure without moisture and degassed in vacuum. Silicon vaseline with additions of halogenized alkylsilanes has not proved satisfactory. The encapsuling of the rectifier systems is also briefly described. There are 5 figures, 1 table and 15 references: 3 Czech, 1 Soviet, 2 German and 9 English. ASSOCIATION: ČKD Praha, n.p., závod Stalingrad

(CKD Prague, Stalingrad Plant)

SUBMITTED:

July 20, 1960 Card 6/6

VINOPAL, Jaromir, inz., dr.; POSA, Gustav, inz.

Methods of chemical etching of germanium and silicon. El tech obzor 51 no.1:46-47 Ja \*62.

43019

8/194/62/000/010/041/084 A061/A126

347000

AUTHORS:

Vinopal, Jaromir, Piša, Gustav

TITLE:

A method of obtaining the structure of the type  $p^+-n-n^+$  or  $n^+-p-p^+$  for silicon power rectifiers

PERIODICAL:

Referativnyy zhurnal, Avtomatika i radioelektronika, no. 10, 1962, 26, abstract 10-4-51ch P (Czech pat., cl. 21g, 11/02, no. 99437, April 15, 1961)

TEXT: It is noted that junctions are formed by alloying, the alloys used for their fabrication being applied in the form of foils 0.05 - 0.2 mm thick. A foil containing silver, antimony, tin, and germanium is applied to one side, and another containing aluminum, indium, and zinc is applied to the otherside of the silicon plate. The two electrodes of the forthcoming rectifier, which are made of tungsten, molybdenum, or tantalum, are also coated with a foil containing, e.g., silver and germanium. The entire multilayer system is annealed at 820-970 C in inert or reducing atmosphere, and is subsequently cooled in the course of 7 - 10 min. The rectifiers thus obtained have a reverse current <0.5 ma at 1,000 v. [Abstracter's note: Complete translation]

Card 1/1

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9.2150 (also 1138,1159)

E073/E535

AUTHORS:

Vinopal, Jaromír, Engineer Doctor and Pisa, Gustav,

Engineer

TITLE

Silicon Power Rectifiers

PERIODICAL: Elektrotechnický obzor, 1960, Vol.49, No.5, pp.268-271

Development work on silicon power rectifiers has been in progress at CKD, Prague, Stalingrad Plant, since 1958. The first stage covered development of P-N junctions for ratings of 100 A and peak voltages of 600 V. The aim was to obtain a P+\_N-N+ junction as proposed by R. N. Hall and W. C. Dunlap (P-N Junctions Prepared by Impurity Diffusion, Phys. Rev. (1950), No.80, p.467). The rectifier system is produced by alloying one side of the silicon plate with an alloy containing primarily silver and a low content of antimony as the donor, and the other side of the plate with an alloy containing primarily aluminium, which acts as an acceptor. As a result P+ and N+ zones are formed on the two faces of the silicon plate with a central high resistance N zone formed by the silicon. For manufacturing the P-N junctions, single-crystal silicon of N-type conductivity, with a specific resistance of 84 to 127  $\Omega$  cm (average value 106  $\Omega$  cm), was used with an average lifetime of the minority carriers of  $134~\mu\text{sec.}$ Card 1/5

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Silicon Power Rectifiers

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Table 1 gives measured values of the voltage drop in the forward direction, V for forward currents of 100 and 150 A. respectively, and of the inverse current,  $\mu \textbf{A}_{\star}$  for inverse voltages 100 to 800 V. The voltage drop in the forward direction corresponds to the usual values for such cells. The volt-ampere characteristic in the forward direction is plotted in Fig. 3. The active surface of the cell can be loaded up to 100 A/cm<sup>2</sup>. In a number of cases inverse currents less than 10  $\mu$ A/cm<sup>2</sup> were obtained for voltages of 1500 V. From the point of view of thermal stability it is advisable to have a low inverse current. For the time being an inverse current of 1 mA/cm2 of the junction at 600 V, measured at normal temperature, is considered to be the maximum permissible limit, the voltampere characteristic in the inverse direction is plotted in Fig. 4. Fig. 5 shows the temperature dependence of the volt-ampere characteristic. In accordance with measured results the developed If the cooling rectifier cells can be loaded up to 140 to 150°C. air temperature is high, the load must be appropriately reduced. The over-load capacity was tested using sinusoidal current pulses of 0.01 sec duration. The starting temperature was 20°C, the

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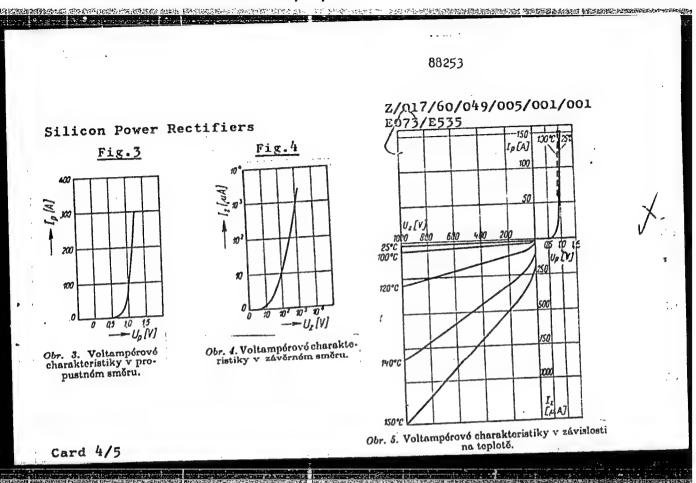
Silicon Power Rectifiers

tested cell withstood a surge of 2150 A but it was destroyed by a surge of 2400 A. By means of the applied technology 80% yield was obtained of satisfactorily etched junctions, of which 70% were diodes with inverse voltages of 600 V and 10% were diodes with Work is in progress for inverse voltages between 300 and 600 V. developing industrial series of silicon rectifiers for the following applications: mine traction (275 V, 500 A); a.c. locomotives (750 V, 4000 A); electrolysis plants for chlorine and aluminium manufacture (450 V, 25 000 A); urban traction (660 V, 1000 A). In conclusion it is stated that the large area P-N silicon junctions are produced in Czechoslovakia without using gold for the transition. Development work has progressed to a sufficient extent to permit starting manufacture on a semi-industrial scale of silicon power rectifiers. Industrial manufacture of these will be accelerated and the prices will be fixed to be comparable There are 5 figures, with foreign rectifiers of the same type. 1 table and 6 references: 3 Czech εnd 3 non-Czech.

ASSOCIATION: CKD Praha - závod Stalingrad (ČKD Prague - Stalingrad Plant)

SUBMITTED: November 29, 1959

Card 3/5



Card 5/5 Silicon Power Rectifiers							88253 Z/017/60/049/005/001/001 E073/E535															
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KROCZEK, J., inz., dr.; VINOPAL, K.; HRUBY, V.

Solenium rectifiers in power industries. Energetika Cz
7 no.2:77-81 F 157.

VINCPAL, K.

Selenium rectifiers in the power industry. p.77.
(Energetika, Vol. 7, No. 2, Feb. 1957, Praha, Czechoslovakia)

So: Monthly List of East Furopean Accessions (EEAL) LC. Vol. 6, No. 9, Sept. 1957. Uncl.

VINOPAL, M., inz.; ECKERTOVA, L., doc. dr.; DEMUTH, M., inz.

Method of gas pressure measurement in closed vacuum systems.

Automatizace 6 no.12:314 D '63.

VINOPAL, S.,

Design characteristics of control valves. p. 239

AUTOMATISACE. (Ceskoslovenska vedecka technicka spolecnost pro elektrotechniku pri Ceskoslovenske akademii ved, Odborna skupina automatisace a Ceskoslocenska spolecost pro sireni politickych a vedeckych znalosti) Praha, Czechoslovakia, Vol. 2, no. 8, Aug. 1959

Monthly List of East European Accessions (EFAI), LC, Vol. 8, no. 10, Oct. 1959 Uncl.

VINOPAL, S.

Design characteristics of control valves. II. p. 272.

AUTOMATIZACE. Praha, Czechoslovakia. Vol. 2, no. 9, Sept. 1959.

Monthly list of East European Accessions (EEAI) LC, Vol. 9, no. 2, Feb. 1960. Uncl.

## VINOPAL, 5.

### TECHNOLOGY

Periodical AUTOMATISACE. No. 11, Nov. 1958.

VINOPAL, S. Flow meters for liquid metals. p. 364.

Monthly List of East European Accessions (EEAI) LC, Vol. 8, no. 3, March, 1959. Uncl.

24695 Z/005/60/000/009/008/015 A121/A126

15.2420

AUTHORS:

Kníze, Bedrich, Engineer, (Nymburk), Raskota, Jan, and Vinopal,

Zdenek (Prague)

TITLE:

None given

PERIODICAL:

Vynálezy, no. 9, 1960, 9

TEXT: (21h, 1; Registered November 24, 1959; Patent Application 6766-59). Sheathing method for ceramic radiators of electricity consuming devices with a ceramic body, formed out directly to the proper shape of electricity consuming device. It is characterized by the following: The body is equipped with a metallic or nonmetallic resistor element, the bare parts of which are covered by a layer of heat-resistant cement. After rendering conductive its surface, such a radiator is metal-coated in a galvanic bath by evaporation or by spraying, by means of which a hermetic and noncorrosive metallic protective coating is obtained.

Card 1/1

VINOSIVASKIY, V.N., dotsent

Selection of the optimum voltage of electric supply systems for coal mines. Izv. vys. ucheb. zav.; gor zhur. no.10:155-158 160.
(MIRA 13:11)

 Kiyevskiy politekhnicheskiy institut. Hekomendovana kafedroy gornoy elektromekhaniki Kiyevskogo politekhnicheskogo instituta. (Electricity in mining)

SOV/112-59-4-6941

2007年2月1日 1000年100日 1000年100日 1000日 1000日

Translation from: Referativnyy zhurnzl. Elektrotekhnika, 1959, Nr 4, p 74 (USSR)

AUTHOR: Vinoslavskiy, V. N.

TITLE: Voltage Regulation in Mine Electric Networks

PERIODICAL: V sb.: Gorn. elektrotekhnika, M., Ugletekhizdat, 1957, pp 476-490

ABSTRACT: Various methods for voltage regulation in mine electric networks are considered; as such networks are mainly supplied by 6-kv lines, the local regulation means are considered preferable. A phase-switching booster transformer is recommended as one of simple and economical devices for local voltage regulation. The transformer permits varying the boost voltage by a step-by-step turning the input-voltage vector with respect to the voltage of a regulated line by means of switching the phases of the supply system. The transformer capacity should amount to 10% of the power transmitted if a 10% regulation is desired. A transformer circuit diagram, a voltage vector diagram, and a description of the regulation scheme are presented, as well as oscillograms of boost-voltage transformer switching, the excitation winding being short-circuited during the switching.

Card 1/1 I.V.Kh.

VINOSLAVSKIY, V. H.

"Booster Transformer with Regulation via Conversion of the Phases of the Dupply Voltage." Min Higher Education USSR, Kiev Order of Lenin of Folytechnic Inst, Electrical Engineering Faculty, Kiev, 1952 (Dissertation for the Degree of Candidate of Technical Sciences)

SO: Knizhnaya Letopis', No. 32, 6 Aug 55

VOLOTKOVSKIY, Sergey Andronikovich, doktor tekhn.nauk; VASILEVSKIY,
Yevgeniy Viktorovich, inzh.; GUTMAN, Emranuil Markovich,
kand. tekhn. nauk; VINOSLAVSKIY, V.N., kand, tekhn.nauk,
retsenzent
[Protection of underground structures from electrolytic corrosion] Zashchita podzemnykh sooruzhenii ot elektrokorrozii.
Kiev, Tekhnika, 1964. 134 p.

(MIRA 17:10)

VINOSLAVSKIY, Vasiliy Mikolayevich, kand.tekhn.nauk,dots.;
RYBCHEKO, Petr Filizonovich, kand.tekhn.nauk,dots.;
POPOVICH, Nikolay Gavrilovich, kand.tekhn.nauk,dots.;
POLYANSKIY, Nikolay Alekseyevich, inzh.; DANIL CHUK,
Grigoriy Ivanovich, inzh.; VOLOTKOVSKIY, S.A., doktor
tekhn. nauk, prof., retsenzent; MIROSHNIK, A.M., kand.
tekhn. nauk, retsenzent; DENISENKO, S.A., inzh.,
retsenzent

[Automation of industrial processes in coal mines] Avtomatizatsiia proizvodstvennykh protsessov ugol'nykh shakht.

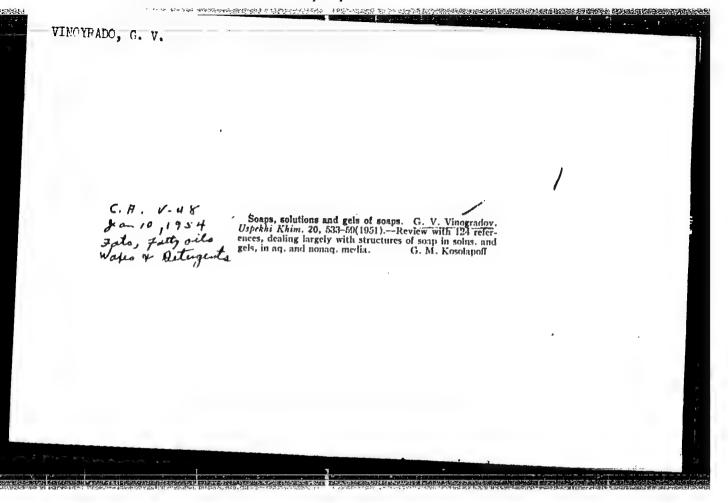
By] V.N.Vinoslavskii i dr. Kiev, Tekhnika, 1964. 406 p.

(MIRA 18:3)

VINCV, M. S.

Dostizhenila sovetskogo produktivnago zkivetnovadalva fachievements of Soviet productive snimal breeding 7. Moskva, Gos. ordena Lenina bria SSSM, 1952. 49 p.

SO: Monthly List of Murai in Acquasions, Vol. 7 No. 2 May 1954.



VINRENZ, Z.

Inaugural address at the 3d National Conference of Scientific and Technological Workers in the Field of Steel Construction. p. 12. INZENYRSKE STAVBY. (Ministerstvo stavebnictvi) Praha.
Vol. 4, no. 1, Jan. 1956

SCURCE: EEAL LC Vol. 5, No. 10 Oct. 1956

VINS, Bohuslav, inz., CSC.

Report on the state and preliminary evaluation of the Czechoslovak test areas of the provenance tests with the spruce of the 128 international series. Les cas 9 no. 12: 1145-1152 D 163.

 Vyzkumny ustav lesniho hospodarstvi a myslivosti, Zbraslav-Strnady.

VI.S. is.

AGR CULTURE

PERTODICALS SCHORNIK REDA LESNICAVI VOL 5, no. 2, Feb. 1959

Vins, B. Preliminary results of experiments on the regeneration of firs. p. 175.

Monthly List of East Eurorean A coessions (EEAI), LC, Vol. 7, No. 6, May 1959, Unclass.

#### "APPROVED FOR RELEASE: 09/01/2001

CIA-RDP86-00513R001860020005-9

30909-66 EWT(1)/FCC ACC NR. AP6022947 SOURCE CODE: CZ/0085/65/000/005/0152/0155 27 AUTHOR: Vins Bohuslay B ORG: Forestry and Game Management Research Institute (VU les. hosp. a mysl.) TITIE: Problems of dendroclimatological research SOURCE: Meteorologicke zpravy, no. 5, 1965, 152-155 TOPIC TAGS: forestry, plant growth, meteorology, climatology ABSTRACT: The article discusses how the fluctuation of the width of the annual rings of trees depends on the influence of weather factors and thereby presents the possibility of investigating those influences on trees in the past. It gives an account of the history, problems and methods of the scientific areas which study the width of annual rings from various points of view (dendrochronological and dendroclimatological research). The method is used above all in forest investigations and practice. but also in many other areas -- meteorology, climatology, astronomy, even archeology and other areas. [JPRS] SUB CODE: 04.02 / SUBM DATE: none / ORIG REF: 016 / SOV REF: 007 OTH REF: 030 Cord 1/1 CC

VINS, Bohuslav, inz. CSc.

Standardization of provenance research and testing. Les cas 10 no.2:216-218 F '64

1. Vyzkumny ustav lesniho hospodarstvi a myslivosti, Zbraslav-Strnady.

VINS, J., inz.; SUIC, J., inz.

Gliding quality of plain bearings with galvanically coated linings. Strojirenstvi 12 no.4:271-277 Ap 162.

1. Statni vyzkumny ustav tepelne techniky (for Vins). 2. Statni vyzkumny ustav ochrany materialu, Praha (for Sulc).

Vins, J.					7	
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	W 22577 United Bushi MI (Czech.) 845-847. Strength, plastics. of bushin	Jse of Plastics With Fings. Fourth Versen/eh. J. Vins. Strojirenstvi, v. pressability, and mach Maximum louds, mount gs and hearings of these	tkanie na kluaria ul tkanie na kluaria ul 5, no. 11, Nov. 19 inability of fabric-reir ing, lubrication, and materials, Tables, gra-	forced colling this.	X PAN	
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VINS, Jindrich, inz.

"Axial ring packing" by E. Mayer. Reviewed by Jindrich Vins.

Stroj vyr 12 no.1:75 Ja'64.

VINS, Karel, inz.

Semiconductors in industry. Tech prace 15 no.9:672-675 S'63.

1. Vyzkumny ustav pro sdelovaci techniku A.S.Popova.

VIII	27.5m245 BY 1940	its. Claborroudy	

23569 Z/009/61/000/007/002/004 E112/E135

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Vinš, Luděk AUTHOR:

Purification of hydrogen with liquid nitrogen TITLE:

PERIODICAL: Chemický průmysl, 1961, No.7, pp. 348-353

Advantages of the purification of hydrogen (required for the synthesis of ammonia) by means of liquid nitrogen are discussed and compared with the conventional method, based on copper salts. A recent Soviet study (Ref.2: I. Burlačenko,

Symposium, MCHP, Prague, 1957) detailing the economic superiority of the liquid nitrogen purification of hydrogen (produced by gasification of brown coal) Basic principles of H2-purification with liquid N2 are reviewed and standard plant equipment is discussed. The process comprises gradual cooling of crude hydrogen, leading to a partial condensation of the impurities. Essential preliminary treatment consists of complete removal of CO2 to prevent icing of the heat exchangers. Cooling the crude hydrogen to -190 °C causes condensation of the methane fraction, the quantity and composition of which depends upon the composition of the entering gas. Carbon monoxide, oxygen, argon and last traces of methane are removed by Card 1/8

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Purification of hydrogen with liquid ... E112/E135 washing with liquid nitrogen at -190 °C in special column. The purified hydrogen-nitrogen mixture leaves at the upper end of the column while the so-called CO-fraction accumulates at the bottom. Different types and designs of the nitrogen cooling cycles are described. The economics of the cooling process are improved by increased  $N_2$ -pressure and a graph is included in which  $N_2$ consumption is plotted versus pressure. The effect of temperature in the washing column upon nitrogen consumption is also shown in the form of a graph, indicating a decrease of  $N_2$ -consumption with a decrease in temperature. The merits of different N2 cooling cycles in the U.S.A. and in Europe are discussed. The author considers that the system developed by Messer of Frankfurt, Germany, offers definite advantages, based as it is on air separation at a pressure of 40 atm. A Czechoslovak design for hydrogen purification with liquid nitrogen (for  $NH_3$  production) is discussed. Sources of  $H_2$ will be either catalytic cracking of natural gas or decomposition of natural gas with simultaneous formation of acetylene. Flow sheets of both processes are submitted. The latter method gives rise to hydrogen of very high methane content. It is therefore necessary to isolate and recycle the methane fraction. Card 2/8

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Purification of hydrogen with liquid ... E112/E135

The Czechoslovak plant is designed to process 14000 to 16000 Nm3 crude hydrogen per hour. The crude H2 enters the plant at a pressure of 12 atm. Particular attention was paid to the prevention of icing of the heat exchangers. Water vapours with which the entering hydrogen is saturated are removed by means of countercurrent exchangers, de-iced by the entering gas, and in ammonia refrigerators, defrozen by means of warm ammonia. The last traces of moisture are removed by absorption on silica gel at -45 °C. Carbon dioxide is also absorbed on silica gel. With maintenance problems in mind the plant was so designed that all heat exchangers can be disconnected and separately defrozen. High-pressure N2 is passed through twin heat exchangers and an absorber, in order to remove traces of contaminating oil. To compensate for the increase of temperature during processing, an open, high-pressure N2 cooling cycle (pre-cooled to -45 °C with ammonia) was operated, as it was assumed that a cooling system based on throttled expansion was simpler and more reliable than a cycle with an expansion machine. For the cooling cycle only such quantities of technological nitrogen are used, as are essential for the washing of hydrogen with liquid Card 3/8

23569 Z/009/61/000/007/002/004 P112/E135

Purification of hydrogen with liquid ... E112/E135 A diagrammatic representation of the plant for  $\mathrm{H}_2$ purification is shown in Fig. 6: (la, lb - entrance heat exchangers, 2 - separator, 3a, 3b - refrigerators, 4 - drier, 5, 6 - heat exchangers, 7 - evaporator of the CO-fraction, 8 - washing column, 9, 10, 11 - heat exchanger, 12 - drier, 13a, 13b - ammonia refrigerators, 14a, 14b - heat exchangers). Hydrogen enters the plant at +20 to +35 °C under a pressure of 12 atm. It is saturated with water vapours and precooled to -30 °C in the heat exchangers la, lb, by means of the recycled hydrogen-nitrogen mixture. Further refrigeration to -40 - -45 °C is accomplished in two ammonia refrigerators, 3a and 3b. A part of the water vapour is eliminated in drier 4 (Abstractor's note: not marked in sketch but obviously is the smaller container between 3b and 5), by means of silica-gel. Cooled nitrogen is then sent to the deep-freeze section, to be refrigerated in heat exchanger 5 and 6 to -170 °C by means of the recycled hydrogen-nitrogen mixture. The crude hydrogen is finally cooled to -190 °C in the evaporator of the CO-fraction (7). Final purification of hydrogen is carried out in wash tower (8) by means of liquid nitrogen, which is being sprayed down to meet the incoming hydrogen. The CO-fraction accumulates Card 4/8

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Purification of hydrogen with liquid ... E112/E135 at the lower end of the tower and methane and argon are completely removed from the hydrogen. The nitrogen required for the purification and refrigeration enters the unit under a pressure of 180-200 atm. It is sent through heat exchangers 14a and 14 b where cooling is effected by means of the CO-fraction. It is further cooled to -45 °C in one of the ammonia refrigerators, 13a or 13b and passes through a silica-gel drier (12) to be freed completely of moisture or oil contaminants. Before entering the deep-freeze section, the nitrogen is divided in two parts; fraction 1 is cooled in heat exchanger 9 by means of the COfraction, while fraction 2 is refrigerated in exchanger 10 by means of the nitrogen-hydrogen mixture. Its temperature is brought down to -170 °C, while final refrigeration to -190 °C is accomplished by throttled expansion. The Czechoslovak plant operates with two heat exchangers for each operation, which are used alternately, permitting removal of the ice without interrupting the process. The heat exchangers, a photograph of which is shown, are of the finned tube type. The following economic data are tabulated:

Card 5/8

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Purification of hydrogen with liquid...E112/E135

Purification of mydrogen was	Consumption for 100 Nm <sup>3</sup> $3 H_2 + N_2$ (11 atm)	for 1 ton
Nitrogen, total, in Nm3 Nitrogen for washing	32 7.45 8	880 204 218
Energy, in kW/h (compression of N <sub>2</sub> and NH <sub>3</sub> ) Energy, in kW/h (for purification of H <sub>2</sub> )	4.1	112
(TOT but Trans		

It is concluded that the design, construction and operation of the new plant for the purification of hydrogen with liquid nitrogen is more economical than scrubbing with a solution of copper, permitting the reduction of processing costs for the production of synthetic ammonia. It is considered to be equal in construction and assumed parameters to similar plants in foreign countries. It is hoped that the equipment will be not only an essential part of the Czechoslovak plants for synthetic ammonia, but will also become an important export item.

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Purification of hydrogen with liquid... E112/E135

There are 7 figures (5 graphs, 2 flow diagrams, 1 sketch of plant-design, 1 photograph of heat exchanger), 3 tables and 9 references; 3 English, 3 German, 2 Czech and 1 Soviet. The English language references read as follows:

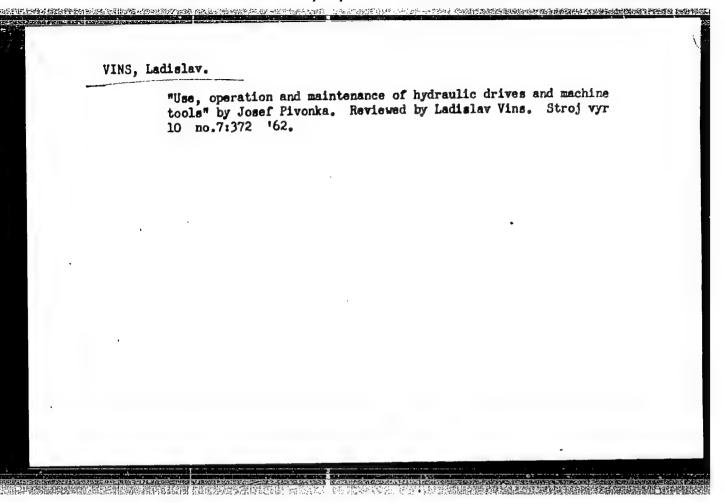
Ref.4: Baker: Low-temperature processes. Chem.Eng.Progr., 51, No.9 (1955), pp. 399-402.

Ref.7: Chow: Phase equilibria for a complex mixture. Proc. Roy. Soc., Ser. A, 192 (1948), pp. 340-364.

Ref.9: The operators report on safety in air and ammonia plants. Chem. Eng. Progr., 55, No.9 (1959), pp. 49-54.

ASSOCIATION: Závody Vítězného února, n.p., Hradec Králové ("Victorious February" Works, Hradec Králové)

Card 7/8



BABKA, V.; VINS, L.

Special high-speed wrenches. Stroj vyr 9 no.12:624-625 '61.

1. Tona, n.p., Pecky (for Babka) 2. Zavody 9. kvetna, n.p., Praha (for Vins)

(2) 1.1 18.20 (1) 2.6.20 (2)

VINS, L.

Design and production of single-purpose machines in factories. p.200. (Strojirenska Vyroba, Vol. 5, No. 5, May 1957, Praha, Czechoslovakia)

SC: Monthly List of East European Accessions (FEAL) LC. Vol. 6, No. 9, Sept. 1957. Uncl.

VINS, L.

Machine for boring holes in the brake drums of motorcycles.

P. 322 Vol. 3, no. 8, 1955 STROJIRENSKA VYROBA Praha, Czechoslovakia

Source: Monthly List of East European Accesions, (EEAL), LC, Vol. 5, no. 2 February 1956, Uncl.

THE, L.

Single purpose machines and American automatic production lines.

P. 30%, (Strojirenska Vyroba) Vol. 5, no. 7, July, 1957, Praha, Caechoslovakia

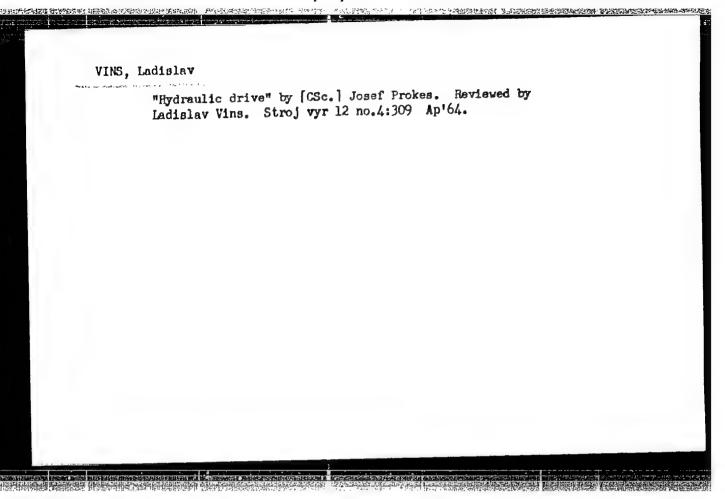
50: Monthly Index of East European Acessions (SEAI) Vol. 6, No. 11 November 1957

VINS, L.

VINS, L. Air press and its use. p. 113

Vol. 4, no. 3, Mar. 1956 STROJIRENSKA VYROBA TECHNOLOGY Praha, Czechoslovakia

So: East European Accession Vol. 6, no. 2, 1957



Fresent situation of glass fiber spatis. Sklar a herenia 14 no. 7600-204 Ji '64.

1. Dieptra Manienal Enterprise, Turnov.

VINS, V.

"Abstract of the traffic rules for driving Pioneer motorcycle." p. 766

SVET MOTORU. Praha, Czechoslovakia, Vol. 9, No. 24, Nov., 1955

Monthly List of East European Accessions (EFAI), LC, Vol. 8, No. 9, September, 1959 Unclas

VINS, V.

Third in Europe. p.280, (Svet Motoru. Praha. Vol. 11, no. 9, Apr. 1927.)

So: Monthly List of East European Accessions (EEAL) LC., Vol. 6, no. 7, July 1957. Uncl.

VINS, V.

(bk) Motor vehicles on the installment plan. p. 284. (Svet Motoru. Praha. Vol. 11, no. 9, Apr. 1957.)

SO: Monthly List of East European Accessions (EEAL) LC., Vol. 6, no. 7, July 1957. Uncl.

Vins. V.

Vins, V. Attention: winter! p. 141.

V. R. Socialist competition in winter maintenance of highways. p. 141.

Ht. The Hvezda 500, formula 3. p. 142.

Vol. 10, no. 5, Mar. 1956 SVET MOTCRU TECHNOLOGY Czechoslovakia

So: Fast European Accessions, Vol. 6, May 1957

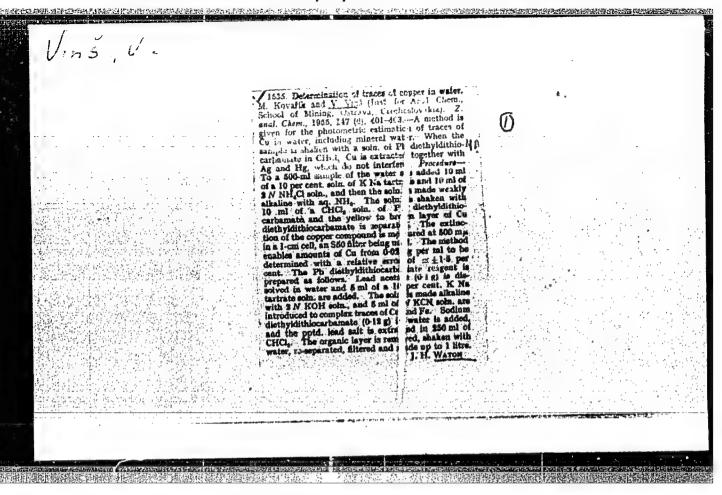
TO A CONTRACTOR VENT DESCRIPTION AND THE PROPERTY OF THE PARTY OF THE

Vins, V.

Vins, V. Traffic signs and highways. p. 571.

Vol. 10, no. 18, Aug. 1956 SVET MOTORU TECHNOLOGY Czechoslovakia

So: East European Accessions, Vol. 6, May 1957
No. 5



WITE, V.

Explaining and om hasizing the right of through traffic. p. 375.
Learning about the transitional types of JAMA-C2 motorcycles. (To be contd.)
p. 376.

SVET MOTORN, Praha, Vol. 9, no. 12, June 1955.

SO: Monthly List of Mast European Accessions, (EMAL), LC, Vol. 4, no. 10, Cct. 1955, Uncl.

"Record of the year of 1953." (p. 216).
"What you don't know about the protective shield." (p.217). SVETA MOTORU (Swaz pro spolupraci s armadou) Praha, Vol 8, No 7, Apr. 1954.

SO: East European Accessions List, Vol 4, No 8, Aug 1954

WINS, V.

"Renewal of Drivers' Licenses." p. 679 (STET MOTORU. Vol. 8, No. 22, Oct. 195h; Praha, Czech.)

So: Monthly List of East European Accessions, (FEAL), LC, Vol. 4, No. 4, April 1955, Uncl...

VINS, V.

"Traffic Accidents Caused by Pcor Lighting." p. 43 (Svet Motoru, Vol. 7, no. 133, Jan. 1953, Preha)

East European Vol. 3, No. 3

No. 1954, Uncl.

VINS, V.

"New and changed traffic regulations." (To be contd.) p. 550 (Svet Motoru, Vol. 7, No. 154, Sept. 1953, Praha)

SO: Monthly List of East European Accessions, Vol. 3, No. 6, Library of Congress, June. 1954, Uncl.

VINS, V.

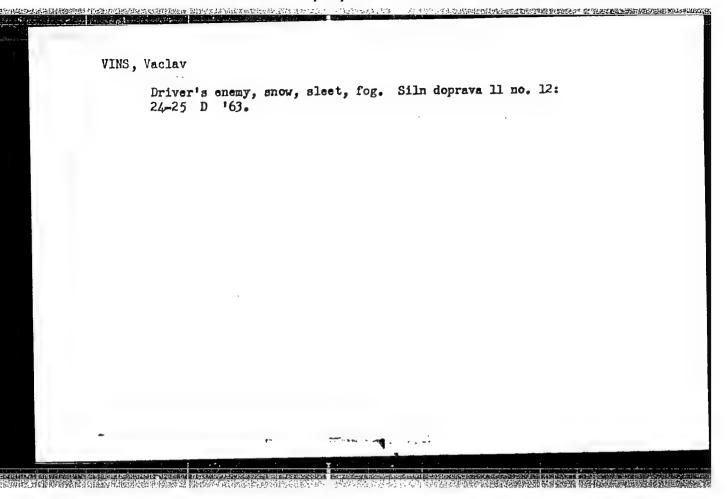
"New Year's Resume." p. 18 (Svet Motoru, Vol. 7, no. 137, Jan. 1953, Fraha)

SO: Monthly List of East Furopean Accessions, Vol. 3, no. 2, Library of Congress, Feb. 1954, Uncl.

VINS, Z.

Preventive maintenance of the BEKK device for testing the smoothness and air permeability of paper. p.109. (Papir A Celulosa, Vol. 12, No. 5, May 1957, Praha, Czechoslovakia)

SO: Monthly List of East European Accessions (EEAL) LC. Vol. 6, No. 9, Sept. 1957. Uncl.



K-5

1. 1.

CZECHOSLOVAKIA/Cherical Technology. Chemical Products and

their Applications. Cellulose and Cellulose

Products. Paper.

Abs Jour: Ref Zhur-Khimiya, 1958, No 1, 3312

Author : Vins Zd.

Inst Title

· Preventive Maintenance of Bekk's Device for Determining

Paper Smoothness and Permeability to Air.

Orig Pub: Papir a celulosa, 1957, 12, No 5, 109-110

Abstract: It is pointed out that correct operation of the device

is upset by the formation of an amalgam. The basic

rules and practical directions for the correct mainten-

ance of the device are considered.

Card : 1/1

MIKOL'SKIY, Yu.N., inzhener; BELEVITSKIY, A.M., inzhener; VINSHTEYN, E.S., inzhenen

Kilms with conveyer calcinaters put in operation at the Krivoy Reg
cement mill. TSement 22 no.2:12-14 Mr-Ap '56. (MRA 9:9)
(Krivey Reg--Cement industries) (Kilms, Rotary) (Conveying machinery)

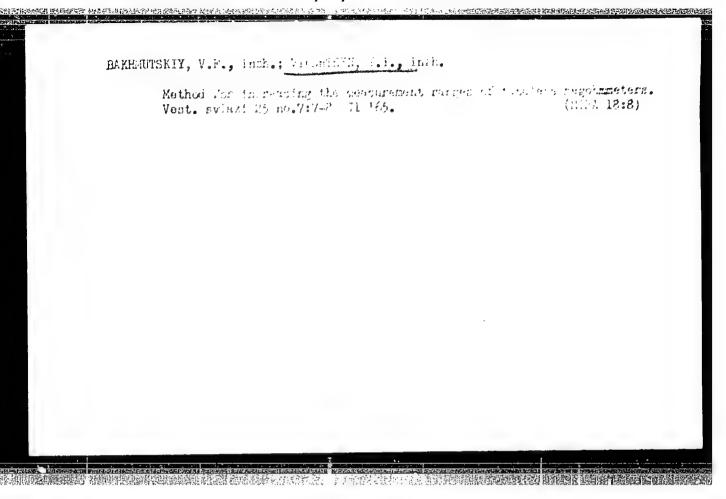
ANISIMOV, N.M.; AREF'YEV, V.A.; VINSHTEYN, E.S.; ZATSEPELIN, V.G.

Pneumatic mixing of raw mixes. TSement 26 no.5:19-22 S-0 '60,
(MIRA 13:10)
(Krivoy Rog--Cement plants)

(Mixing machinery)

MESH, L.Ya.; KAMINER, D.M.; VINSHTEYN, I.I.

Temperature regulator based on a self-excited self-oscillator.
Avtom. i prib. no. 1:59-60 Jt-Mr 164. (MIRA 17:5)



ACCESSION NR: AP4020321

5/0302/64/000/001/0059/0060

AUTHOR: Mesh, L. Ya.; Kaminer, D. M.; Vinshteyn, I. I.

TITLE: Temperature controller based on a self-excited oscillator

SOURCE: Avtomatika i priborostroyeniye, no. 1, 1964, 59-60

TOPIC TAGS: temperature controller, dc temperature controller, transistorized temperature controller, thermistor temperature controller, transportation type temperature controller

ABSTRACT: The shortcomings of dc-supplied temperature controllers are briefly reviewed: "bimetallic sensors are unstable while dilatometric switches often do not ensure necessary reliability because of microleakages..."; dc amplifiers are unstable particularly in the -40+50C range; dc-ac conversions complicate the system. Free from the above drawbacks — as claimed by the authors — is a new temperature controller based on a transistorized oscillator

Card 1/2

ACCESSION NR: AP4020321

with phase-controlled self-excitation; the controller is intended for mobile installations. The oscillator is excited only in the case where the unbalance voltage of a thermistor-containing bridge has a certain phase relation to the voltage of the oscillator emitters. A differential gap of 2-3C is ensured by a positive feedback. Tests showed that, within 40 to 450C, the set point drifts by only 0.2C; and the differential by only 0.3C. The change in threshold sensitivity caused by aging of elements and ambient temperature variation has hardly any effect on controller operation. Orig. art. has: 1 figure.

ASSOCIATION: none

SUBMITTED: 00

DATE ACQ: 31Mar64

ENCL: 00

SUB CODE: IE

NO REF SOV: 000

OTHER: 000

Card 2/2

BAKHMUTSKIY, V.F. (L'vov); VINSHTEYN, I.I. (L'vov); SAS, S.Ye., (L'vov)

Use of impulse power supply for measurement bridge circuits with semiconductor thermistor in devices of two-position temperature control. Autom. i telem. 22 no.2:259-262 F '61. (MIRA 14:4) (Bridge circuits) (Temperature regulators)

9,6000 (1040,1089,1099)

\$/103/61/022/002/013/015 B019/B060

AUTHORS: Bakhmutskiy, V. F., Vinshteyn, I. I., Sas, S. Ye. (L'vov)

TITLE:

Use of a pulse feeding of a measuring bridge with semiconductor thermistors in two-position temperature control devices

PERIODICAL: Avtomatika i telemekhanika, w. 22, no. 2, 1961, 259-262

TEXT: A study has been made of the heat balance of a semiconductor thermistor with pulse feeding. By way of introduction, setup and use of two-position temperature control devices are discussed in general. The investigation proper is made on the basis of the diagram shown in Fig. 1. This diagram consists of the pulse generator IC, the measuring circuit MK, the semiconductor thermistor ST, and the two-position indicator TT. The following relations are given for the power dissipation in the thermistor with pulse feeding:

$$p(t) = \begin{cases} P & \text{with } n(t_p + t_1) \le t \le (t_p + t_1) + t_1 \\ 0 & \text{with } n(t_p + t_1) + t_1 \le t \le (n+1)(t_p + t_1) \end{cases}$$
(1)

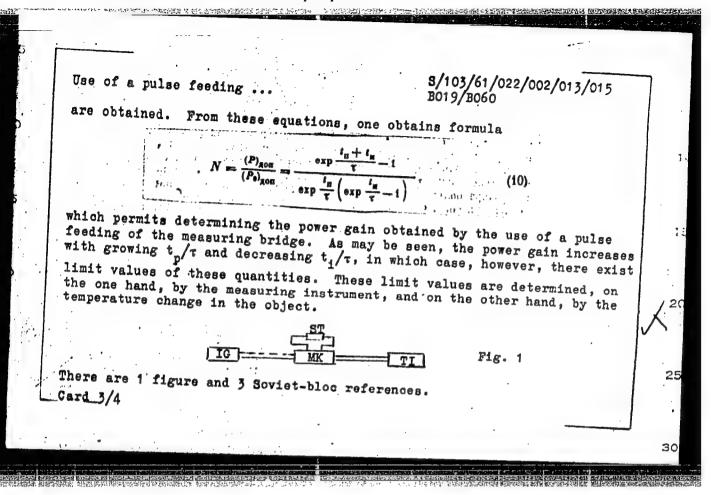
card 1/4

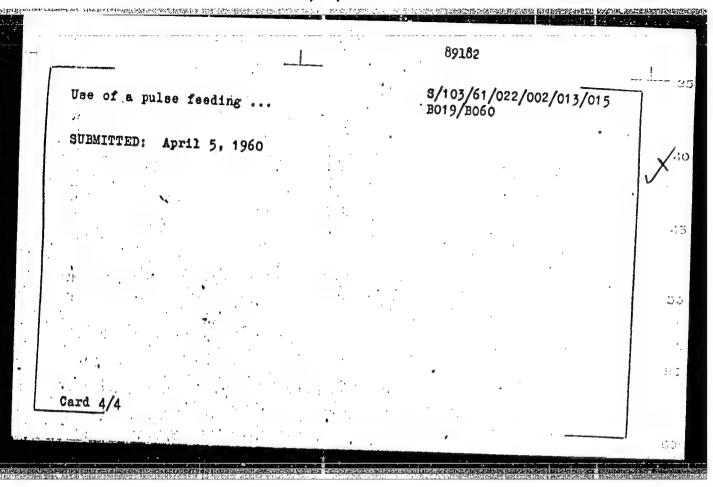
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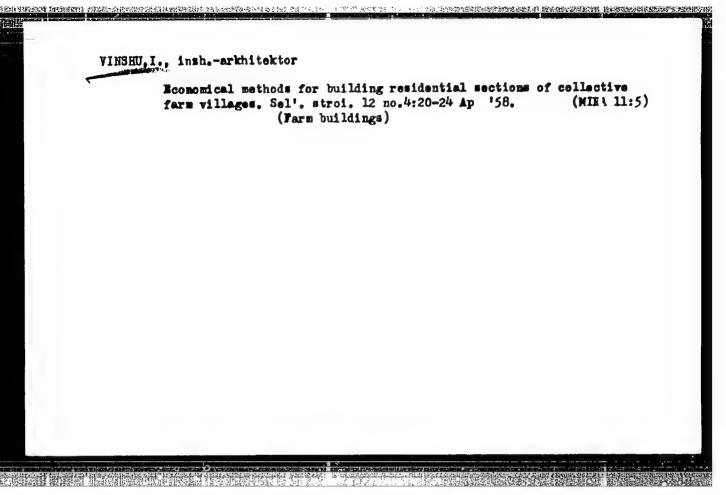
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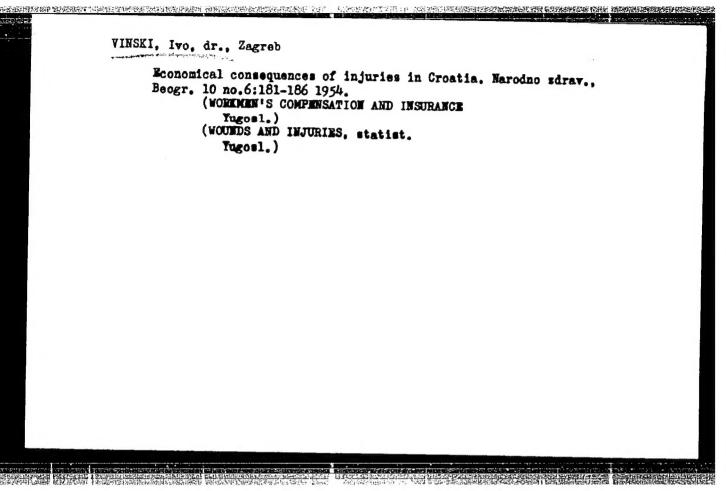




VINSKI, Ivo, dr. naucni savjetnik (Zagreb, Nemciceva 2)

Growth of capital assets of Yugoslavia in the postwar period. Tehnika Jug 18 no.1:17-24 Ja 963.

1. Ekonomski institut NR Hrvatske, Zagreb.



VINSKIY, A., general-mayor inzhenernykh voyek.

Colonel Petrov, commander of an engineering unit and Hero of the Soviet Union. Voen.-inzh. zhur. 101 no.10:28-29 0 '57. (MIRA 10:11) (Petrov, Ivan Vasil'evich)

Cross cut	Gross cutting for mounting shields. Mast.ugl. 6 no.9:14 5 '57. (MIRA 10:11)			
1. Wachal	1. Nachal'nik uchastka shakhty imeni Vakhrusheva (Mine timbering)			

中国公共2017年1月1日的日本中国企图社会区域和国际的国际的国际社会通过1918年1月1日的国际国际国际国际国际国际国际国际国际国际国际国际国际国际国际国际国际

KOTASEK, A.; VINSOVA, N.; BENDL, J.; CERVENKA, J.; CECHME, E.

Perinatal mortality in late gestoses. Cesk. gynek. 29 no.6:470-478 Ag '64.

1. Gyn.-por. klin. fak. vseob. lek. Karlovy University v Praze (prednosta prof. dr. K. Klaus, DrSc.) a II. gyn.-por. klin. fak. vseob. lek. Karlovy University v Praze (prednosta prof. dr. J. Lukas, DrSc.).